

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI AJT085** is Designed for

**FEATURES:**

- Input Matching Network
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	8.0 A
<b>V<sub>CC</sub></b>	40 V
<b>P<sub>DISS</sub></b>	300 W @ T <sub>C</sub> ≤ 100 °C
<b>T<sub>J</sub></b>	-65 °C to +250 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	0.75 °C/W

**PACKAGE STYLE .400 2NL FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F		.193 / 4.90
G		.450 / 11.43
H		.125 / 3.18
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

**ORDER CODE: ASI10547**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 25 mA	55			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 25 mA    R <sub>BE</sub> = 10 Ω	55			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	3.5			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 35 V			20	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V    I <sub>C</sub> = 2.0 A	20		200	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 50 V    P <sub>OUT</sub> = 85 W    f = 960 – 1215 MHz	7.5			<b>dB</b>
<b>η<sub>c</sub></b>		40			<b>%</b>